

09/923,058

**Clean Copy of Specification Paragraphs As Amended By This Response****• New Title:**

METHODS FOR ENHANCING SILICON DIOXIDE TO SILICON NITRIDE  
SELECTIVITY

**• New Abstract:**

A<sub>1</sub>  
A process for controlling the plasma etch of a silicon dioxide layer at a high etch rate and high selectivity with respect to silicon nitride, particularly in a multilayer structure, by (1) maintaining various portions of the etch chamber at elevated temperatures, and/or (2) using an etch chemistry having a fluorohydrocarbon gas containing at least as many hydrogen atoms as fluorine atoms, preferably CH<sub>2</sub>F<sub>2</sub> or CH<sub>3</sub>F.

**• New paragraph at page 1, line 4:**

A<sub>2</sub>  
This is a continuation application of co-pending U.S. Application Serial Number 09/344,277, filed June 30, 1999, which issued as U.S. Patent Number 6,287,978 on September 11, 2001; which was a continuation of U.S. Applicant Serial Number 08/905,891, filed August 4, 1997, which issued as U.S. Patent Number 6,015,760 on January 18, 2000; which was a continuation of U.S. Application Serial Number 08/152,755, filed November 15, 1993, which issued as U.S. Patent Number 5,880,036 on March 9, 1999; which was a continuation-in-part of U.S. Application Serial Number 07/898,505, filed June 15, 1992, which issued as U.S. Patent Number 5,286,344 on February 15, 1994.